PROGRAM TIME TABLE

Tuesday, September 25

9:30-12:15 A. Plenary (Main Hall)

2F B-1	2F B-2	1F C-1	1F C-2	1F D	1F E
13:30-15:15 Area 7: A-1: Silicon Photonics (1): Active Devices	**13:30-14:40 Area 4:** B-1: Volatile Memory	**13:30-15:10 Area 2&:13** C-1: Carbon Interconnect	**13:30-15:20 Area 1:** D-1: High-k MOS	**13:30-15:20 Area 3:** E-1: Nanowire FET	**13:30-15:00 Area 6:** F-1: III-V MOSFETs
15:40-17:25 Area 7: A-2: Silicon Photonics (2) : Fabrication & Materials	**15:40-17:15 Area 4:** B-2: Flash Memory	**15:40-17:10 Area 13:** C-2: Nanowire Growth and Characterization	**15:40-17:30 Area 1:** D-2: Characterization in Gate Stack (1)	**15:40-17:25 Area 3:** E-2: Fin FET	**15:40-17:25 Area 6:** F-2: High Frequency GaN Devices

19:00-21:00《Banquet》(Swan & Garden)

Wednesday, September 26

2F B-1	2F B-2	1F C-1	1F C-2	1F D	1F E
9:00-10:15 Area 7: A-3: Novel Functional Devices	**9:00-10:10 Area 4:** B-3: PRAM/FeRAM	**9:00-10:15 Area 13:** C-3: Nanowire Devices		**9:00-10:10 Area 1&3:** E-3: III-V /Ge MOSFET	**9:00-10:15 Area 6:** F-3: III-V FETs
10:45-12:00 Short Presentation Area 7	**10:45-12:00 Short Presentation** Area 4	**10:45-12:00 Short Presentation** Area 13	**10:45-12:00 Short Presentation** Area 1	**10:45-12:00 Short Presentation** Area 3	**10:45-12:00 Short Presentation** Area 6

13:30-15:00《Poster Session》(Annex Hall)

2F B-1	2F B-2	1F C-1	1F C-2	1F D	1F E
15:25-16:25 Area 7: A-4: Plasmonics and Photonic Crystal Lasers	**15:25-16:35 Area 4:** B-4: ReRAM (1)	**15:25-16:40 Area 8&9&13:** C-4: Graphene Devices	**15:25-16:55 Area 1:** D-4: Post-Si Technology (1)	**15:25-16:45 Area 3:** E-4: Novel Devices	**15:25-16:40 Area 6&14:** F-4: GaN Power Devices (1) (Area 6&14 joint)
17:05-18:05 Area 7: A-5: Photonic Crsytals	**17:05-18:20 Area 4:** B-5: ReRAM (2)	**17:05-18:20 Area 8&9&13:** C-5: Graphene Growth (1)	**17:20-18:20 Area 1:** D-5: Post-Si Technology (2)	**17:05-18:25 Area 3:** E-5: Mobility Enhancement	**17:05-18:20 Area 6&14:** F-5: GaN Power Devices (2) (Area 6&14 joint)

19:00-21:00《Rump Sessions》(RS-A;Room D & RS-B;Room E)

Thursday, September 27

2F B-1	2F B-2	1F C-1	1F C-2	1F D	1F E
9:00-10:45 Area 7: A-6: III-V Photonic Devices	**9:00-10:45 Area 4:** B-6: ReRAM (3)	**9:00-10:45 Area 13:** C-6: CNT Growth and Devices	**9:00-10:20 Area 1:** D-6: Junction Technology	**9:00-10:45 Area 3:** E-6: CMOS Platform	**9:00-10:45 Area 6&14:** F-6: SiC Power Devices (Area 6&14 joint)
11:15-12:45 Area 7: A-7: Silicon Photonics III : Ge-related Devices	**11:15-12:25 Area 4:** B-7: ReRAM (4)	**11:15-12:30 Area 8&9&13:** C-7: Graphene Properties	**10:45-12:15 Area 1:** D-7: Process Technology	**11:15-12:35 Area 3:** E-7: Device Physics	**11:15-12:15 Area 6:** F-7: GaN Interface Characterization
	14:00-15:20 Area 4: B-8: ReRAM (5)	**14:00-15:00 Area 8&9&13:** C-8: Graphene Growth (2)	**14:00-15:20 Area 1:** D-8: Characterization in Gate Stack (2)	**14:00-15:20 Area 3:** E-8: BTI & NOISE	**14:00-15:00 Area 6:** F-8: Thin Film Transistors
				15:40-17:00 Area 3: E-9: Characterization	**15:40-16:55 Area 6:** F-9: GaN Process Technology

Area Scope

Area 1: Advanced LSI Processing & Materials Science
Area 2: Advanced Interconnect / Interconnect Materials and Characterization
Area 3: CMOS Devices / Device Physics
Area 4: Advanced Memory Technology
Area 5: Advanced Circuits and Systems
Area 6: Compound Semiconductor Electron Devices and Related Technologies
Area 7: Photonic Devices and Optoelectronic Integration
Area 8: Advanced Material Synthesis and Crystal Growth Technology
Area 9: Physics and Applications of Novel Functional Devices and Materials
Area 10: Organic Materials Science, Device Physics, and Applications

PROGRAM TIME TABLE

Tuesday, September 25

9:30-12:15 A. Plenary (Main Hall)

1F G	1F H	2F I	2F J	2F K	5F 554	5F 555
13:30-15:15 Area 9: G-1: Optical and Electrical Properties in Nano Materials	**13:30-15:00 Area 15:** H-1: Compound Solar Cells	**13:30-15:00 Area 8:** I-1: Nitrides	**13:30-15:20 Area 5:** J-1: Image Sensor		**13:30-15:15 Area 14:** L-1: Si Power Devices	**13:30-15:15 Area 10:** M-1: OTFT (1): Fabrication and Novel Structures
15:40-17:10 Area 9: G-2: Single Electron Devices	**15:40-17:10 Area 15:** H-2: Crystalline Silicon Solar Cells	**15:40-17:25 Area 8:** I-2: Growth and Characterization of Group IV Related Materials	**15:40-17:30 Area 5&11:** J-2: CMOS- MEMS Modeling & Biomedical Applications	**15:40-17:10 Area 2:** K-2: Future Interconnects (1)	**15:40-17:25 Area 14:** L-2: SiC Processing and Characterization Technology	**15:40-17:25 Area 10:** M-2: OTFT (2): Materials and Characterization

19:00-21:00《Banquet》(Swan & Garden)

Wednesday, September 26

1F G	1F H	2F I	2F J	2F K	5F 554	5F 555
9:00-10:00 Area 9: G-3: ReRam Devices with Nano Dots	**9:00-10:15 Area 15:** H-3: Quantum Dot Solar Cells	**9:00-10:00 Area 8:** I-3: Oxides	**9:00-10:15 Area 5:** J-3: Variation & Reliability	**9:00-10:30 Area 2:** K-3: Future Interconnects (2)	**9:00-10:15 Area 14:** L-3: Diamond Growth and Devices	**9:00-10:15 Area 10:** M-3: OLED and Photonic Devices
10:45-12:00 Short Presentation Area 9	**10:45-12:00 Short Presentation** Area 15	**10:45-12:00 Short Presentation** Area 8	**10:45-12:00 Short Presentation** Area 5&11	**10:45-12:00 Short Presentation** Area 2	**10:45-12:00 Short Presentation** Area 14	**10:45-12:00 Short Presentation** Area 10&12

13:30-15:00《Poster Session》(Annex Hall)

1F G	1F H	2F I	2F J	2F K	5F 554	5F 555
15:25-16:40 Area 9: G-4: Quantum Transport in Nanostructures (1)	**15:25-16:40 Area 15:** H-4: Thin Film Silicon Solar Cells	**15:25-16:40 Area 8:** I-4: Nanostructure Growth	**15:25-16:35 Area 5:** J-4: Sensing & Recognition Systems	**15:25-16:35 Area 2:** K-4: 3D/TSV Interconnect. (1)		**15:25-16:40 Area 10:** M-4: Device Physics : Novel Materials and Functions
17:05-18:20 Area 9: G-5: Quantum Transport in Nanostructures (2)	**17:05-17:50 Area 15:** H-5: New Concept		**17:05-18:25 Area 5:** J-5: Advanced Circuits	**17:05-18:15 Area 2:** K-5: 3D/TSV Interconnect. (2)		**17:05-18:20 Area 10:** M-5: Organic Optoelectronics Devices

19:00-21:00《Rump Sessions》(RS-A;Room D & RS-B;Room E)

Thursday, September 27

1F G	1F H	2F I	2F J	2F K	5F 554	5F 555
	9:00-10:55 Area 2: H-6: Characterization and Advanced Process	**9:00-10:45 Area 11:** I-6: Smart Biomedical Devices	**9:00-10:30 Area 5:** J-6: Wireless Circuits (1)	**9:00-10:45 Area 12:** K-6: Spintronic Devices and Memory		**9:00-10:45 Area 10&15:** M-6: Organic Photovoltaic Devices
		11:15-12:30 Area 11: I-7: Biomedical Imaging Technologies	**11:15-12:15 Area 5:** J-7: Wireless Circuits (2)	**11:15-12:30 Area 12:** K-7: Spintronic Materials		**11:15-11:30 Area 10&15:** M-7: Organic Photovoltaic Devices
		14:00-15:30 Area 11: I-8: Bio-/Nano- Sensors		**14:00-15:15 Area 12:** K-8: Photonics and Quantum Effects		
		15:40-16:55 Area 11: I-9: Lab-on-a-chip and Microfludic devices		**15:40-17:25 Area 12:** K-9: Spins in Semiconductors		

Area 11: Devices and Materials for Biology and Medicine
Area 12: Spintronics Materials and Devices
Area 13: Application of Nanotubes, Nanowires, and Graphene
Area 14: Power Devices and Materials
Area 15: Photovoltaic Materials and Devices